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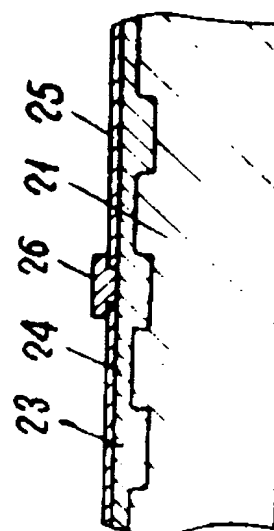
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TITLE : MANUFACTURE OF SOLAR BATTERY



ABSTRACT : PURPOSE: To improve the sensitivity of short wave length and to prevent an increase in leakage current as well by forming an impurity diffusion layer so that a shallow part and a deep part may alternately locate on the main surface of a semiconductor substrate wherein an electrode is provided at the deep part of the diffusion layer.

CONSTITUTION: A diffusion layer 23 is formed by selectively and insularly or beltlike diffusing an impurity, for example, boron which can become acceptor from the main surface of an N-type silicon semiconductor 21. Wherein, the above is done at the first thermal treatment process. Next, a new diffusion layer 24 is formed by connecting the insular or beltlike diffusion layer 23 by the second thermal treatment process. Furthermore, a reflection preventive film 25 is formed by performing annealing treatment in oxide atmosphere. Finally, an electrode 26 is formed at a part of the diffusion layer 23.

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